

forming a photoresist pattern on the metal layer, such that a portion of the metal layer is exposed;

cont. treating the exposed portion of the metal layer with a first plasma, prior to etching, using the photoresist pattern as a mask, to lower a binding force in the exposed portion; and  
A1

etching the treated portion of the metal layer to form a pixel electrode.

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12. (Amended) A method of manufacturing a pixel electrode in a liquid crystal display device, comprising:

depositing a metal layer on a passivation layer which partially covers a transistor;

A2 forming a photoresist pattern on the metal layer, leaving a portion of the metal layer uncovered;

exposing the uncovered portion of the metal layer to <sup>at least one first gas</sup> [a first plasma] prior to etching, to lower a binding force in the uncovered portion; and

etching the uncovered portion of the metal layer with <sup>at least one gas</sup> a second plasma to form a pixel electrode.

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22. (Amended) A method of patterning a metal layer, comprising:

A3 depositing a metal layer over a substrate;

forming a mask on the metal layer, leaving a portion of the metal layer uncovered;

cont. exposing the uncovered portion of the metal layer to a first plasma,  
A3 prior to etching, to lower a binding force in the uncovered portion; and

etching the uncovered portion of the metal layer with a second plasma  
to form a metal pattern.

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